

# Methods for noise calculation of active devices

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For more information



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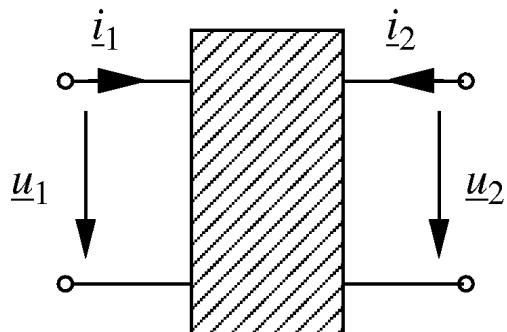
# Overview

- Simulation of noisy n-ports
- Separation of the noise sources
- FET example
- Application example
- Conclusion

# Noisy 2-ports

Transformation matrix

$$[T]^{(y \rightarrow a)} = \begin{bmatrix} 0 & -\frac{1}{y_{21}} \\ 1 & -\frac{y_{11}}{y_{21}} \end{bmatrix}$$



Noise matrix

$$\begin{array}{c} \text{input} \\ \text{output} \end{array} \xrightarrow{\quad} \begin{bmatrix} v_i^{(a)} \\ i_o^{(a)} \end{bmatrix} = [T]^{(y \rightarrow a)} \begin{bmatrix} i_i^{(y)} \\ i_o^{(y)} \end{bmatrix}$$

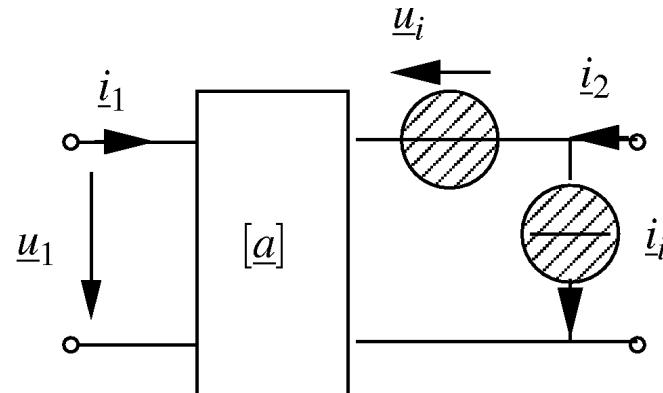


Fig.: Transformation of noise sources.

Correlation matrix, calculation of noise power

$$[\underline{C}]^{(a)} = \frac{1}{4kT\Delta f} \left( \begin{bmatrix} v_i \\ i_o \end{bmatrix} \begin{bmatrix} v_i^* & i_o^* \\ i_o & i_i \end{bmatrix} \right)$$

# Separation of noise sources

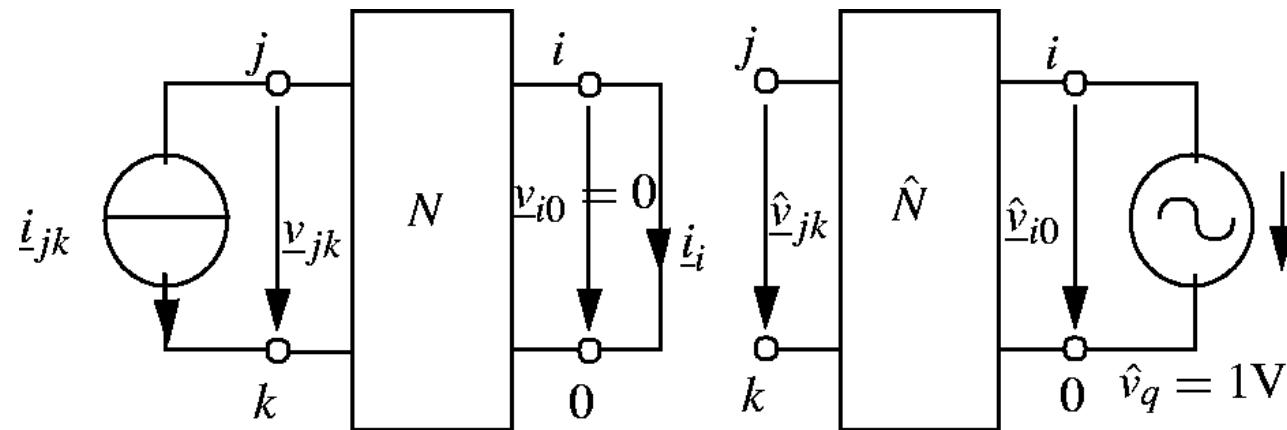


Fig.: Calculation of transformation functions.

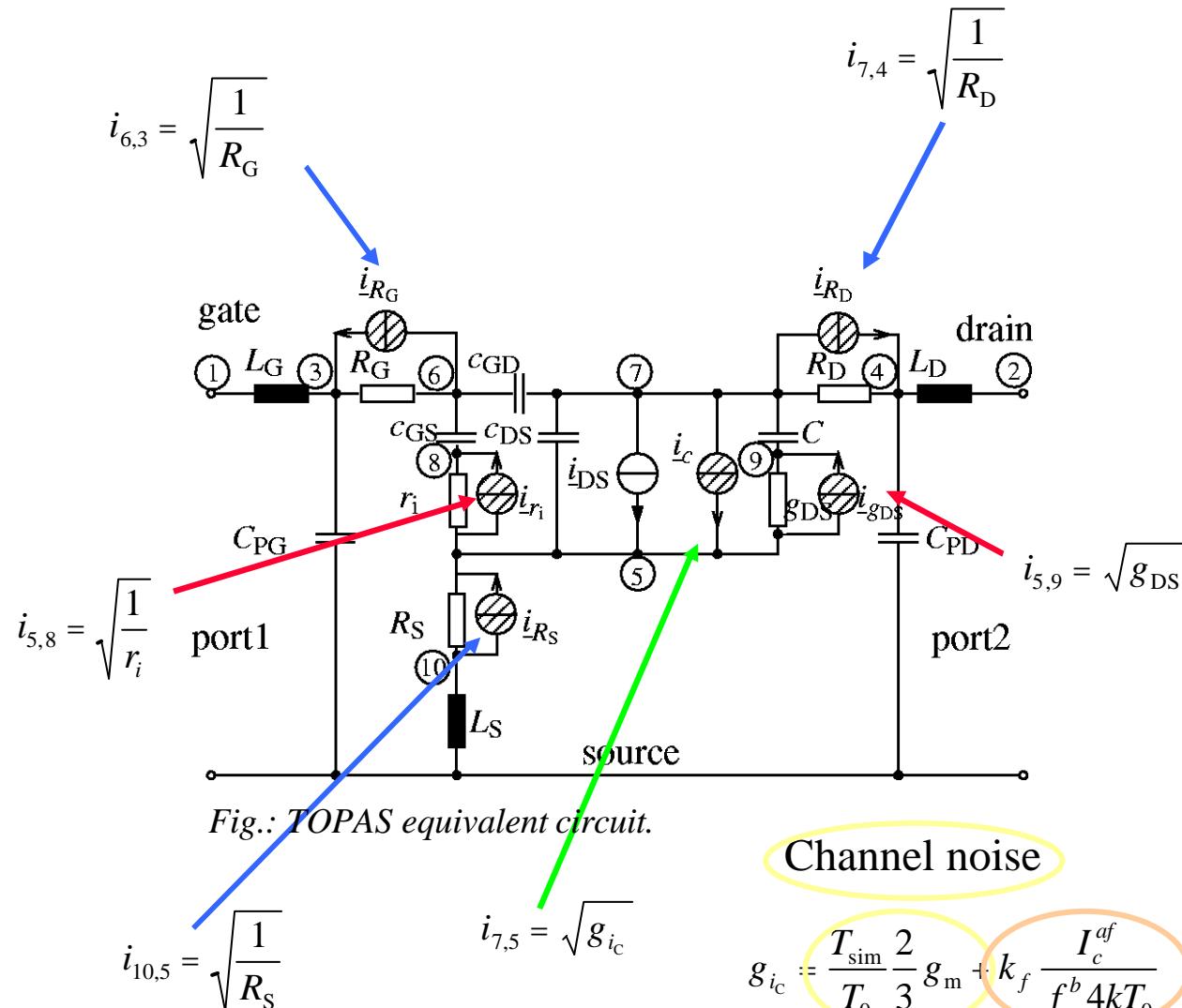
Network N  
Y-matrix

Adjuncted network  
Transposed Y-matrix

Current transformation function

$$\alpha_{i,jk} = \frac{i_i}{i_{jk}} = -\frac{\hat{v}_{jk}}{\hat{v}_q}$$

# FET example



Noise current matrix

$$[i_N] = \sqrt{4kT\Delta f} \cdot$$

0	0	0	0	0	0	0	0	0	0
0	0	0	0	0	0	0	0	0	0
0	0	0	0	0	0	0	0	0	0
0	0	0	0	0	0	0	0	0	0
0	0	0	0	0	0	0	0	0	0
0	0	$i_{6,3}$	0	0	0	0	0	0	0
0	0	0	$i_{7,4}$	$i_{7,5}$	0	0	0	0	0
0	0	0	0	0	0	0	0	0	0
0	0	0	0	0	0	0	0	0	0
0	0	0	0	$i_{10,5}$	0	0	0	0	0

# Tellegen Theorem 1

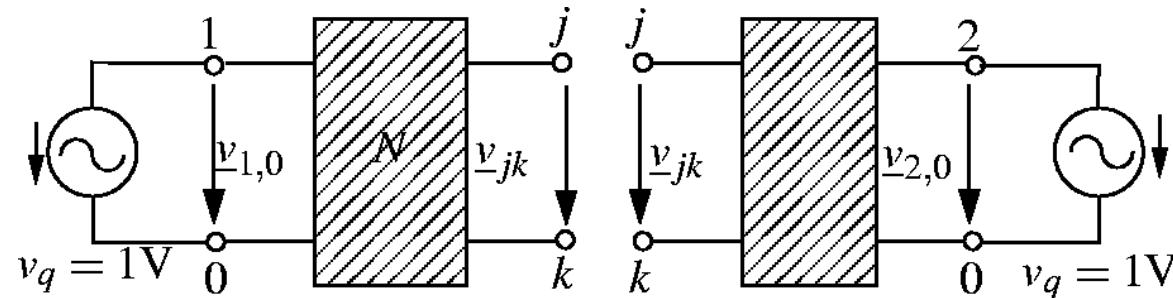
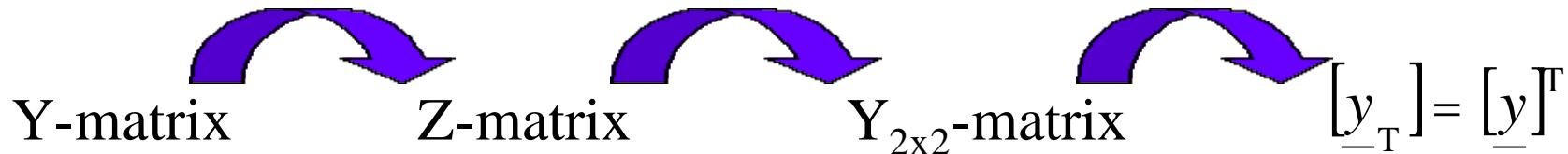


Fig.: Tellegen theorem for noisy circuits.

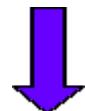
Adjuncted network for calculating transformation functions

$$i_{Q_1} = \frac{v_q}{y_{T,2 \times 2_{1,1}}} \quad \text{and} \quad i_{Q_2} = \frac{v_q}{y_{T,2 \times 2_{2,2}}}$$

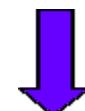
# Tellegen Theorem 2

$$\begin{bmatrix} i_{Q1} \\ \vdots \\ i_{Q10} \end{bmatrix} = \begin{bmatrix} y_{T_{1,1}} & \cdots & y_{T_{1,10}} \\ \vdots & \ddots & \vdots \\ y_{T_{10,1}} & \cdots & y_{T_{10,10}} \end{bmatrix} \begin{bmatrix} v_1 \\ \vdots \\ v_{10} \end{bmatrix}$$

Solve equation system for the voltages using Gauss algorithm



Voltage transformation factor



One single noise source at input, one single at output



$$[T]^{(y \rightarrow a)} = \begin{bmatrix} 0 & -\frac{1}{y_{2 \times 2_{21}}} \\ 1 & -\frac{y_{2 \times 2_{11}}}{y_{2 \times 2_{21}}} \end{bmatrix}$$



1 current, 1 voltage source at output

# Correlation matrix

$$F = 1 - \frac{T_{\text{sim}}}{T_0} \frac{\left| \underline{y}_G \right|^2 C_{11}^{(a)} + C_{22}^{(a)} + 2\Re \left\{ \underline{y}_G \underline{C}_{12}^a \right\}}{g_G}$$

$$R_n = \frac{T_{\text{sim}}}{T_0} C_{11}^a$$

Correlation matrix

$$[\underline{C}]^{(a)} = [T]^{(y \rightarrow a)} [\underline{C}]^{(y)} [T]^{(y \rightarrow a)^+}$$

$$V_{\text{NF}} [\text{dBm} / \sqrt{\text{Hz}}] = \\ 20 \log \left( \sqrt{\frac{T_{\text{sim}}}{T_0} \cdot i_0 i_0^* \frac{50\Omega}{50\Omega \Re \left( \underline{y}_{2 \times 2_{22}} \right) + 1} \cdot 1000} \right)$$

$$\Gamma_{G_{\text{opt}}} = \frac{1 - \underline{y}_{G_{\text{opt}}} Z_0}{1 + \underline{y}_{G_{\text{opt}}} Z_0}$$

# Verification 1

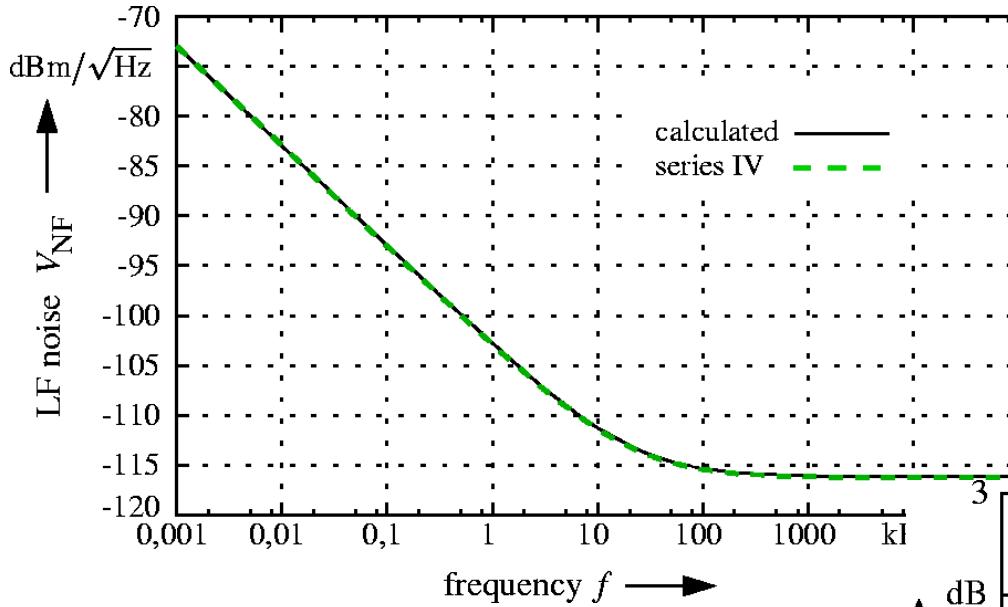
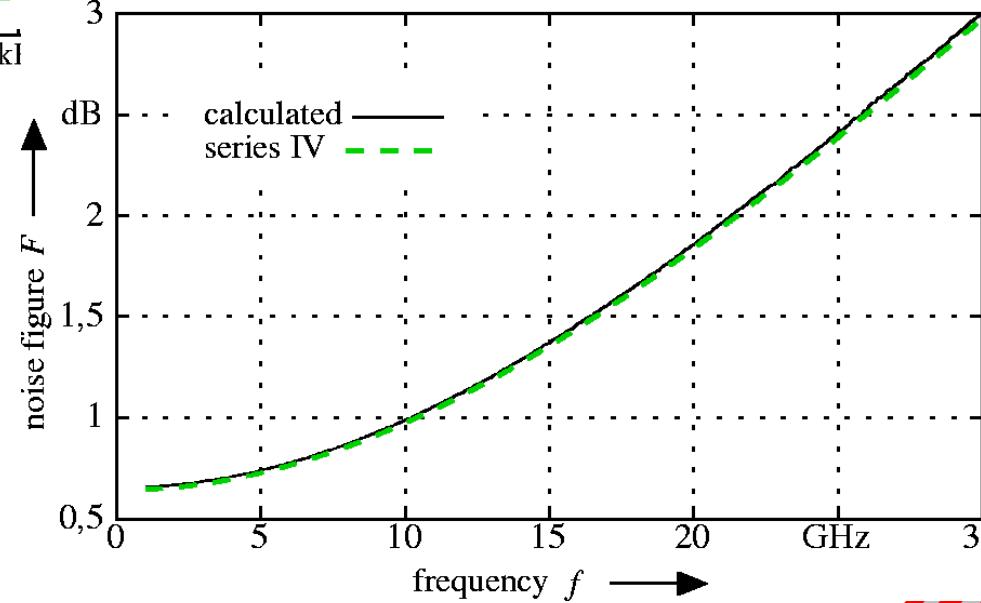


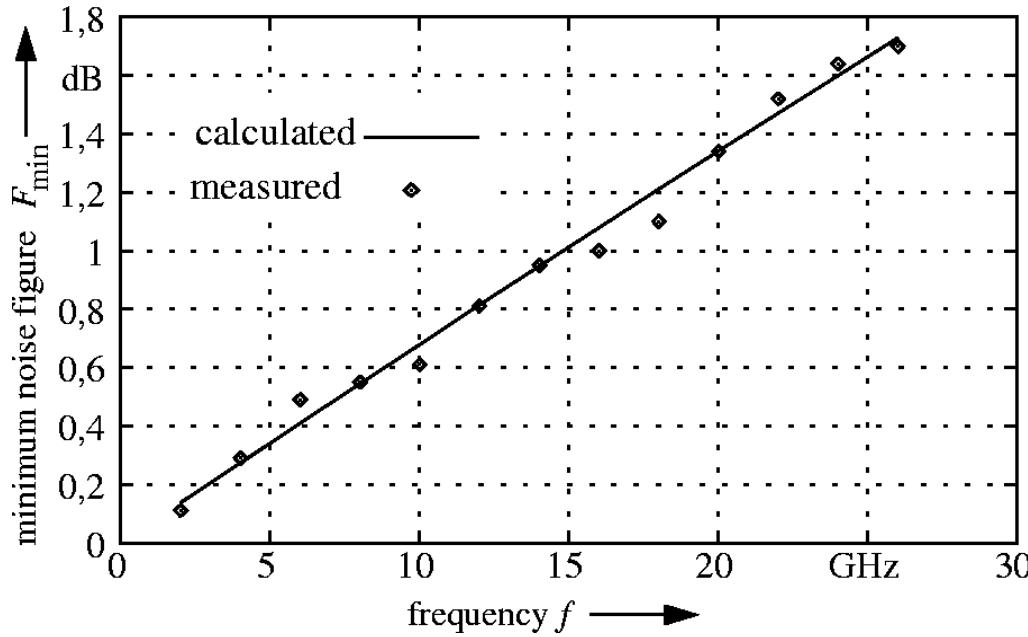
Fig.: Calculation for 1/f-noise. Comparison of proposed algorithm versus series IV simulation.

Fig.: Calculation of noise figure F. Comparison of proposed algorithm versus series IV simulation.



# Verification 2

Fig.: Simulation and measurement of minimum noise figure.



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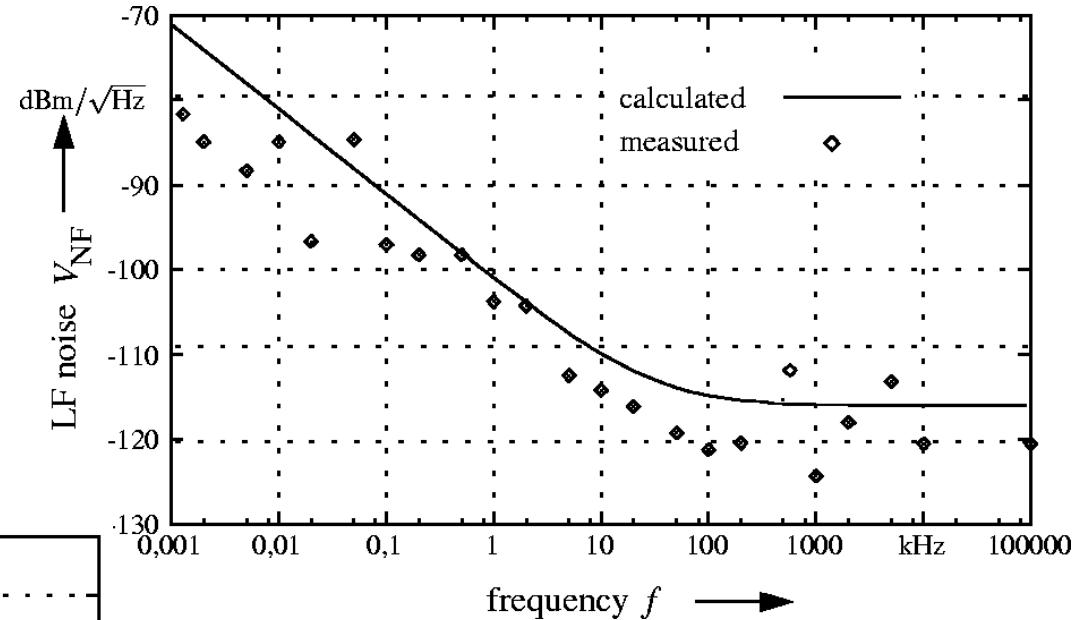


Fig.: Simulation and measurement of  $1/f$ -noise.

# Verification 2

1/f-noise parameter extraction

$$i_f^2 = k_f \frac{I^{af}}{f^b} \Delta f$$

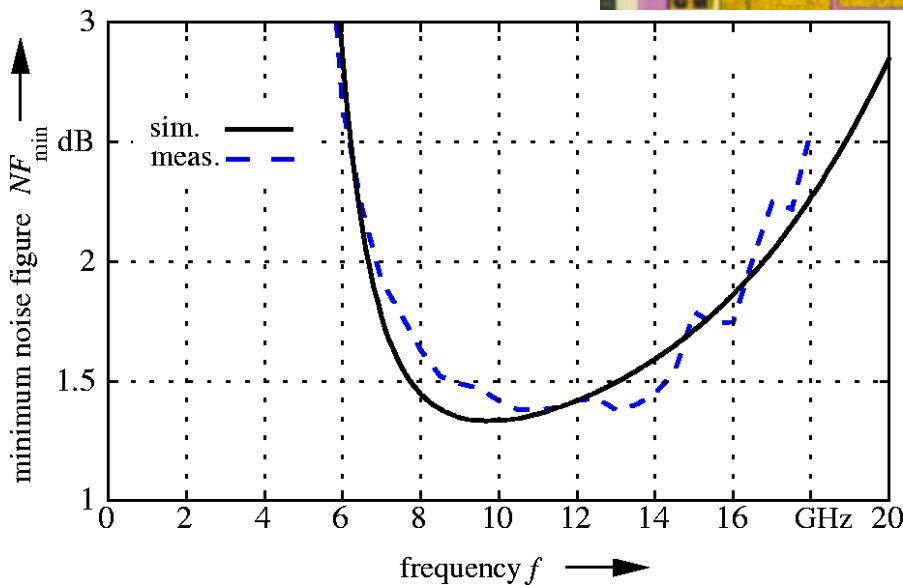


Fig.: Minimum noise figure. Measurement versus simulation.

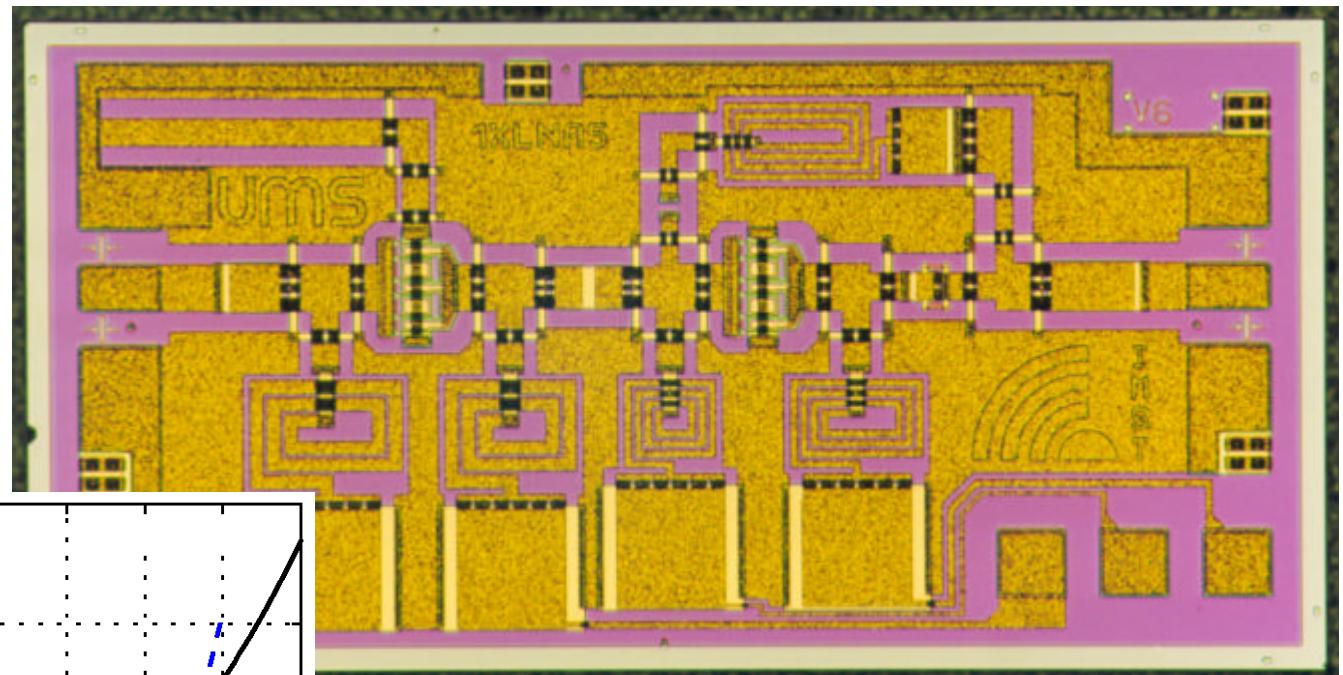


Fig.: Chip photography of the X-band LNA.

# Conclusion

- Fast noise calculation method
- Excellent comparison to commercial available methods (ADS)
- Allows simulation as well as extraction
- LF and RF noise behaviour